

SURFACE MOUNT SILICON DUAL, COMPLEMENTARY TRANSISTOR



Central[®] Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLT2207G consists of one isolated 2N2222A NPN transistor and one complementary isolated 2N2907A PNP transistor, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This device has been designed for small signal general purpose amplifier and switching applications.

MARKING CODE: L7G

• Device is *Halogen Free* by design

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL	<u>NPN (Q1)</u>	<u>PNP (Q2)</u>	UNITS
Collector-Base Voltage	V _{CBO}	75	60	V
Collector-Emitter Voltage	VCEO	40	60	V
Emitter-Base Voltage	V _{EBO}	6.0	5.0	V
Continuous Collector Current	IC		600	mA
Power Dissipation	PD	:	mW	
Operating and Storage Junction Temperature	TJ, Tstg	-65	to +150	°C
Thermal Resistance	Θ_{JA}	:	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

		NPN	<u>(Q1)</u>	PNF	<u>(Q2)</u>	
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
ICBO	V _{CB} =60V	-	10	-	-	nA
I _{CBO}	V _{CB} =50V	-	-	-	10	nA
ICBO	V _{CB} =60V, T _A =125°C	-	10	-	-	nA
ICBO	V _{CB} =50V, T _A =125°C	-	-	-	10	nA
ICEV	V _{CE} =60V, V _{EB(OFF)} =3.0V	-	10	-	-	nA
ICEV	V _{CE} =30V, V _{EB(OFF)} =500mV	-	-	-	50	nA
I _{EBO}	V _{EB} =3.0V	-	10	-	-	nA
BVCBO	I _C =10μΑ	75	-	60	-	V
BVCEO	I _C =10mA	40	-	60	-	V
BVEBO	I _E =10μA	6.0	-	5.0	-	V
V _{CE(SAT)}	I _C =150mA, I _B =15mA	-	0.3	-	0.4	V
V _{CE} (SAT)	I _C =500mA, I _B =50mA	-	1.0	-	1.6	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA	0.6	1.2	-	1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA	-	2.0	-	2.6	V
h _{FE} `´´	V _{CE} =10V, I _C =0.1mA	35	-	75	-	
h _{FE}	V _{CE} =10V, I _C =1.0mA	50	-	100	-	
h _{FE}	V _{CE} =10V, I _C =10mA	75	-	100	-	
h _{FE}	V _{CE} =10V, I _C =150mA	100	300	100	300	
h _{FE}	V _{CE} =1.0V, I _C =150mA	50	-	-	-	
h _{FE}	V _{CE} =10V, I _C =500mA	40	-	50	-	

R5 (29-June 2015)

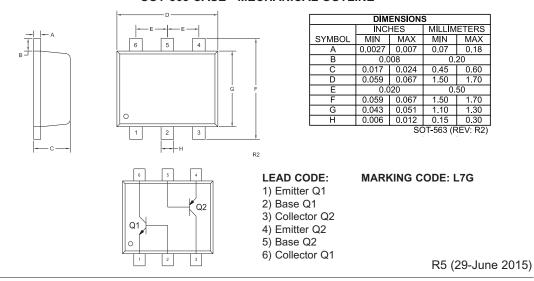


CMLT2207G

SURFACE MOUNT SILICON DUAL, COMPLEMENTARY TRANSISTOR

ELECTRICA	L CHARACTERISTICS - Continued:	NPN	<u>(Q1)</u>	PNF	<u>P (Q2)</u>	
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
fT	V _{CE} =20V, I _C =20mA, f=100MHz	300	-	-	-	MHz
fT	V _{CE} =20V, I _C =50mA, f=100MHz	-	-	200	-	MHz
Cob	V _{CB} =10V, I _E =0, f=1.0MHz	-	8.0	-	8.0	pF
Cib	V _{EB} =0.5V, I _C =0, f=1.0MHz	-	25	-	-	pF
Cib	V _{EB} =2.0V, I _C =0, f=1.0MHz	-	-	-	30	pF
h _{ie}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	2.0	8.0	-	-	kΩ
h _{ie}	V _{CE} =10V, I _C =10mA, f=1.0kHz	0.25	1.25	-	-	kΩ
h _{re}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	-	8.0	-	-	x10-4
h _{re}	V _{CE} =10V, I _C =10mA, f=1.0kHz	-	4.0	-	-	x10-4
h _{fe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	50	300	-	-	
h _{fe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	75	375	-	-	
h _{oe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	5.0	35	-	-	μS
h _{oe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	25	200	-	-	μS
rb'C _C	V _{CB} =10V, I _E =20mA, f=31.8MHz	-	150	-	-	ps
NF	V _{CE} =10V, I _C =100μA, R _S =1.0kΩ, f=1.0kHz	-	4.0	-	-	dB
t _{on}	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA	-	-	-	45	ns
td	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA	-	10	-	10	ns
tr	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA	-	25	-	40	ns
^t off	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	-	-	-	100	ns
ts	V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA	-	225	-	-	ns
ts	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	-	-	-	80	ns
tf	V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA	-	60	-	-	ns
t _f	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	-	-	-	30	ns

SOT-563 CASE - MECHANICAL OUTLINE



www.centralsemi.com

CMLT2207G



SURFACE MOUNT SILICON DUAL, COMPLEMENTARY TRANSISTOR

SERVICES

- · Bonded Inventory
- Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/Multi Discrete Modules (MDM™)
- Bare Die Available for Hybrid Applications

LIMITATIONS AND DAMAGES DISCLAIMER: In no event shall Central be liable for any collateral, indirect, punitive, incidental, consequential, or exemplary damages in connection with or arising out of a purchase order or contract or the use of products provided hereunder, regardless of whether Central has been advised of the possibility of such damages. Excluded damages shall include, but not be restricted to: cost of removal or reinstallation, rework, ancillary costs to the procurement of substitute products, loss of profits, loss of savings, loss of use, loss of data, or business interruption. No claim, suit, or action shall be brought against Central more than two (2) years after the related cause of action has occurred.

In no event shall Central's aggregate liability from any warranty, indemnity, or other obligation arising out of or in connection with a purchase order or contract, or any use of any Central product provided hereunder, exceed the total amount paid to Central for the specific products sold under a purchase order or contract with respect to which losses or damages are claimed. The existence of more than one (1) claim against the specific products sold to Buyer under a purchase order or contract shall not enlarge or extend this limit.

Buyer understands and agrees that the foregoing liability limitations are essential elements of a purchase order or contract and that in the absence of such limitations, the material and economic terms of the purchase order or contract would be substantially different.

R5 (29-June 2015)

www.centralsemi.com